

Technical Data Sheet

3mm Phototransistor T-1

PT204-6C

Features

- Fast response time
- High photo sensitivity
- Pb free
- The product itself will remain within RoHS compliant version.

Descriptions

- PT204-6C is a high speed and high sensitive NPN silicon phototransistor molded in a standard $\phi 3$ mm package. Due to is water clear epoxy the device is sensitive to visible and near infrared radiation.

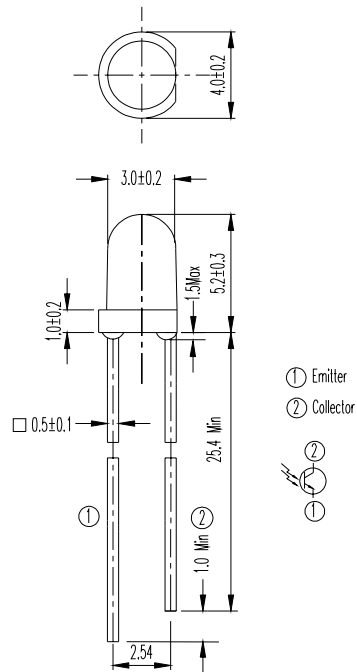


Applications

- Infrared applied system
- Camera
- Printer
- Optoelectronic switch

Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
PT	Silicon	Water clear

Package Dimensions

- Notes:** 1.All dimensions are in millimeters
2.Tolerances unless dimensions ± 0.25 mm

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Collector-Voltage	V_{ECO}	5	V
Collector Current	I_C	20	mA
Operating Temperature	T_{opr}	-25 ~ +85°C	°C
Storage Temperature	T_{stg}	-40 ~ +85°C	°C
Lead Soldering Temperature *1	T_{sol}	260	°C
Power Dissipation at (or below) 25°C Free Air Temperature	P_c	75	mW

- Notes:** *1:Soldering time ≤ 5 seconds.
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Electro-Optical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Rang Of Spectral Bandwidth	$\lambda_{0.5}$	---	400	---	1100	nm
Wavelength Of Peak Sensitivity	λ_p	---	---	940	---	nm
Collector – Emitter Breakdown Voltage	BV_{CEO}	$I_C=100\ \mu A$ $E_e=0mW/cm^2$	30	---	---	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	$I_E=100\ \mu A$ $E_e=0mW/cm^2$	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2mA$ $E_e=1mW/cm^2$	---	---	0.4	V
Rise Time	t_r	$V_{CE}=5V$ $I_C=1mA$ $RL=1000\ \Omega$	---	15	---	μS
Fall Time	t_f		---	15	---	
Collector Dark Current	I_{CEO}	$E_e=0mW/cm^2$ $V_{CE}=20V$	---	---	100	nA
On State Collector Current	$I_{C(on)}$	$E_e=1mW/cm^2$ $V_{CE}=5V$	0.7	2.0	---	mA

Rankings

Parameter	Symbol	Min	Max	Unit	Test Condition
G	$I_{C(ON)}$	0.70	1.90	mA	$V_{CE}=5V$ $E_e=1mW/c\ m^2$
H		1.14	2.60		
J		1.77	3.61		
K		2.67	5.07		

Typical Electro-Optical Characteristics Curves

Fig.1 Collector Power Dissipation vs.
Ambient Temperature

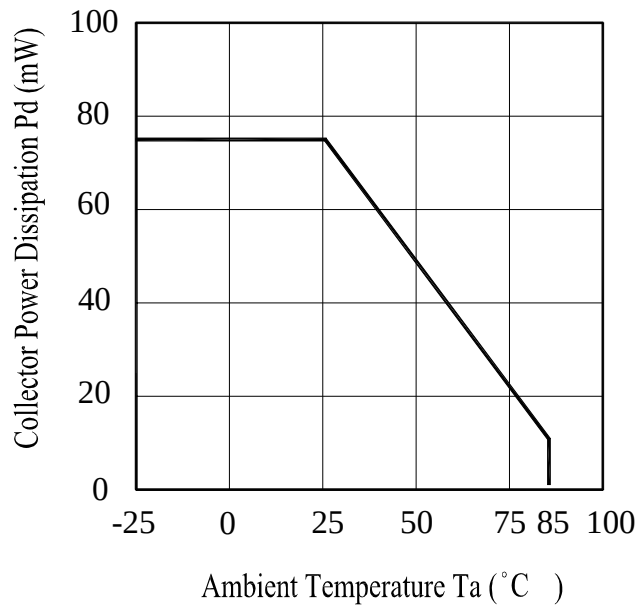


Fig.2 Spectral Sensitivity

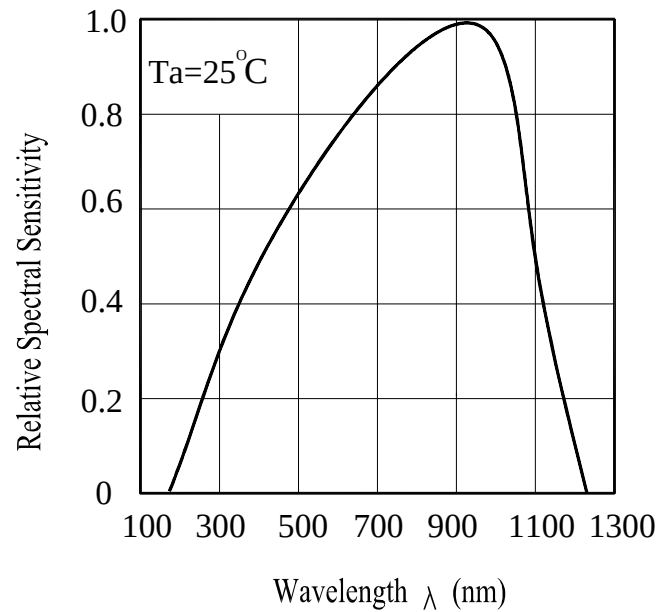


Fig.3 Relative Collector Current vs.
Ambient Temperature

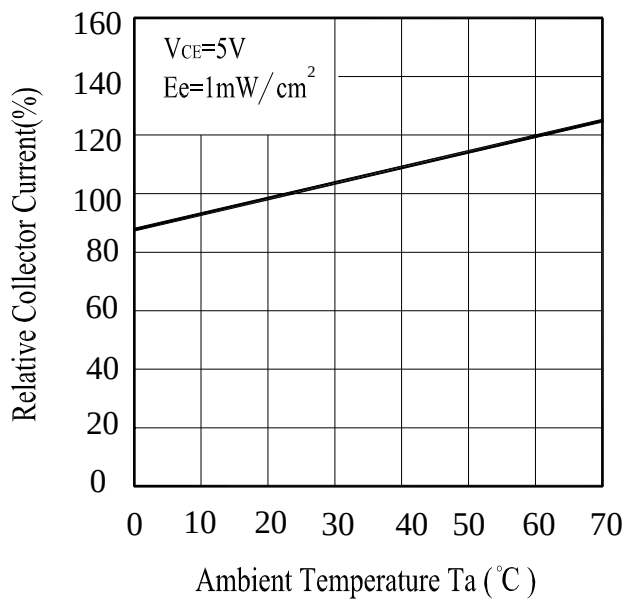
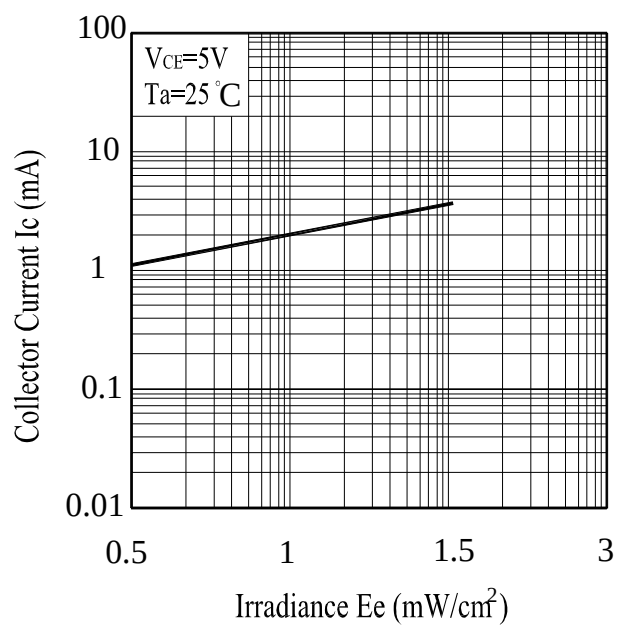


Fig.4 Collector Current vs.
Irradiance



Typical Electro-Optical Characteristics Curves

Fig.5 Collector Dark Current vs.

Ambient Temperature

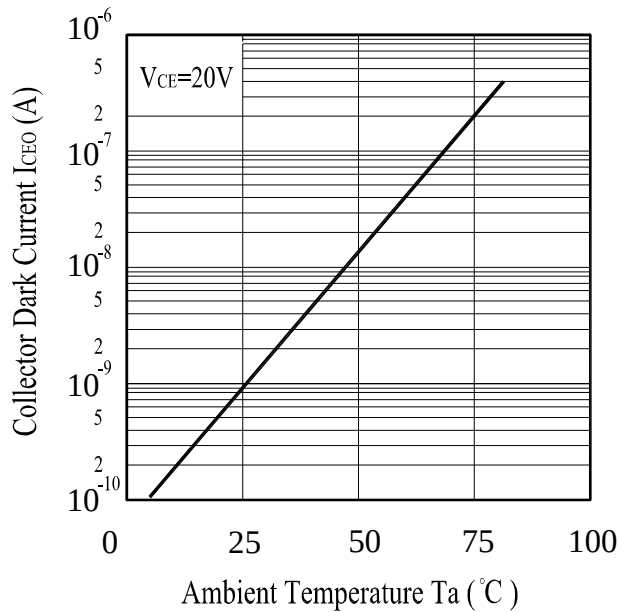
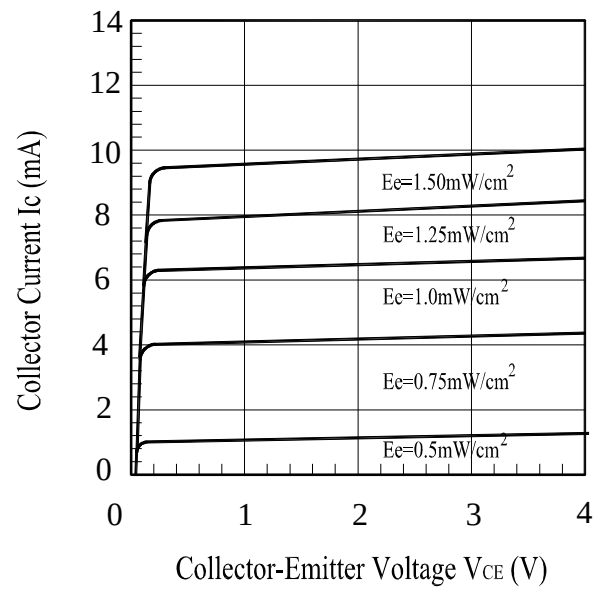


Fig.6 Collector Current vs.

Collector-Emitter Voltage



Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP. : $260^{\circ}\text{C} \pm 5^{\circ}\text{C}$	10secs	22pcs	$I_{C(ON)} \leq L \times 0.8$ L : Lower Specification Limit	0/1
2	Temperature Cycle	H : $+100^{\circ}\text{C}$ 15mins ↓ 5mins L : -40°C 15mins	300Cycles	22pcs		0/1
3	Thermal Shock	H : $+100^{\circ}\text{C}$ 5mins ↓ 10secs L : -10°C 5mins	300Cycles	22pcs		0/1
4	High Temperature Storage	TEMP. : $+100^{\circ}\text{C}$	1000hrs	22pcs		0/1
5	Low Temperature Storage	TEMP. : -40°C	1000hrs	22pcs		0/1
6	DC Operating Life	$V_{CE}=5\text{V}$	1000hrs	22pcs		0/1
7	High Temperature/ High Humidity	85°C / 85% R.H	1000hrs	22pcs		0/1

Packing Quantity Specification

1.1000PCS/1Bag , 4Bags/1Box

2.10Boxes/1Carton

Label Form Specification

EVERLIGHT	
CPN:	
P/N:	
	RoHS
QTY:	PT204-6C
	CAT:
LOT NO:	HUE:
	REF:
MADE IN TAIWAN	

PN: Customer's Production Number

P/N : Production Number

QTY: Packing Quantity

CAT: Ranks

HUE: Peak Wavelength

REF: Reference

LOT No: Lot Number

MADE IN TAIWAN: Production Place